CGD1040HI

1 GHz, 20 dB gain GaAs high output power doubler Rev. 01 — 22 September 2009 Produc

Product data sheet

Product profile

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

1.2 Features

- Excellent linearity
- Superior levels of ESD protection
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Compliant to Directive 2002/95/EC, regarding Restriction of the use of certain Hazardous Substances (RoHS)
- Integrated ring wave surge protection

1.3 Applications

■ CATV systems operating in the 40 MHz to 1003 MHz frequency range

1.4 Quick reference data

Quick reference data

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 ^{\circ}\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		-	20	-	dB
		f = 1003 MHz		19.5	20.8	22.0	dB
СТВ	composite triple beat	$V_0 = 56.4 \text{ dBmV}$ at 1003 MHz	[1]	-	-74	-64	dBc
CCN	carrier-to-composite noise	$V_0 = 56.4 \text{ dBmV}$ at 1003 MHz	[1]	57	63	-	dBc
I _{tot}	total current		[2]	-	440	460	mΑ

^{[1] 79} NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

[2] Direct Current (DC).



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2. Pinning information

Table 2. Pinning

	3	
Pin	Description	Simplified outline Graphic symbol
1	input	
2, 3	common	1 3 5 7 9
5	+V _B	
7, 8	common	12/3/7/8
9	output	sym095

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
CGD1040HI	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 × 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{B}	supply voltage			-	30	V
$V_{i(RF)}$	RF input voltage	single tone		-	75	dBmV
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	<u>[1]</u>	-	2000	V
		Biased; According IEC61000-4-2		-	1500	V
T _{stg}	storage temperature			-40	+100	°C
T_mb	mounting base temperature			-20	+100	°C

^[1] The ESD pulse of 2000 V corresponds to a class 2 sensitivity level.

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5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 \text{ V (DC)}$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 \degree C$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		-	20	-	dB
		f = 1003 MHz		19.5	20.8	22.0	dB
SL _{sl}	slope straight line	f = 40 MHz to 1003 MHz	<u>[1]</u>	0.5	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 1003 MHz	[2]	-	-	1	dB
RL_{in}	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		16	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
RLout	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		16	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
NF	noise figure	f = 50 MHz		-	5	6	dB
		f = 1003 MHz		-	5.5	6.5	dB
I _{tot}	total current		[3]	-	440	460	mΑ
79 NTSC	channels + 75 digital channels						
СТВ	composite triple beat	V _o = 56.4 dBmV at 1003 MHz	<u>[4]</u>	-	-74	-64	dBc
CSO	composite second-order distortion	V _o = 56.4 dBmV at 1003 MHz	<u>[4]</u>	-	-78	-65	dBc
Xmod	cross modulation	V _o = 56.4 dBmV at 1003 MHz	<u>[4]</u>	-	-68	-	dB
CCN	carrier-to-composite noise	V _o = 56.4 dBmV at 1003 MHz	<u>[4]</u>	57	63	-	dBc
79 NTSC channels							
СТВ	composite triple beat	V _o = 58.4 dBmV at 1003 MHz	[5]	-	-70	-	dBc
CSO	composite second-order distortion	V _o = 58.4 dBmV at 1003 MHz	[5]	-	-76	-	dBc
Xmod	cross modulation	V _o = 58.4 dBmV at 1003 MHz	[5]	-	-66	-	dB

^[1] G_p at 1003 MHz minus G_p at 40 MHz.

^[2] Flatness is defined as peak deviation to straight line.

^[3] Direct Current (DC).

^{[4] 79} NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

^{[5] 79} NTSC channels [f = 54 MHz to 550 MHz]; tilt extrapolated to 13.5 dB at 1003 MHz.

6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

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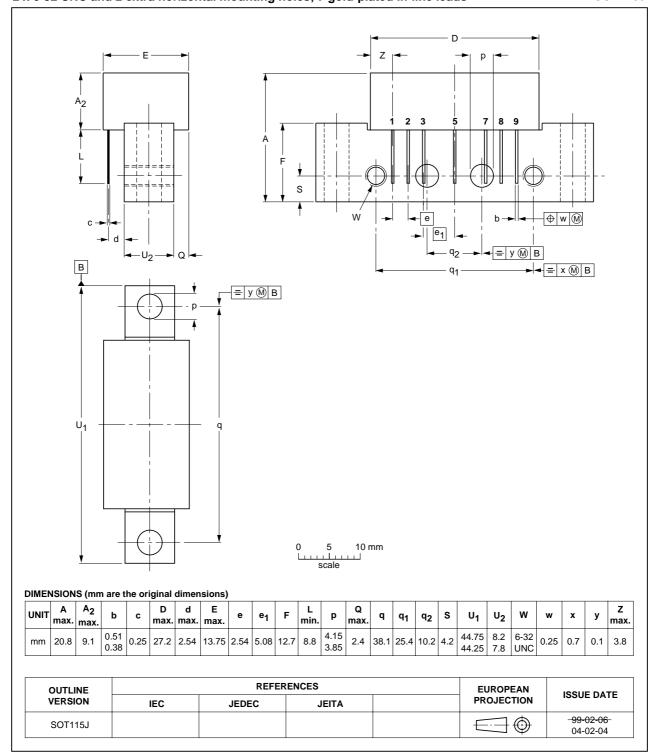


Fig 1. Package outline SOT115J

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7. Abbreviations

Table 6. Abbreviations

Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
RF	Radio Frequency
UNC	UNified Coarse

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD1040HI_1	20090922	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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1 GHz, 20 dB gain GaAs high output power doubler

11. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information
4	Limiting values 2
5	Characteristics 3
6	Package outline 4
7	Abbreviations 5
8	Revision history 5
9	Legal information 6
9.1	Data sheet status 6
9.2	Definitions6
9.3	Disclaimers 6
9.4	Trademarks6
10	Contact information 6
11	Contents

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